

Features

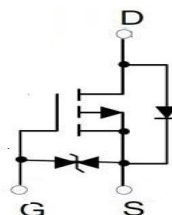
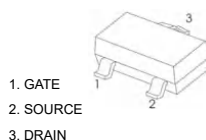
Surface Mount Package
P-Channel Switch with Low RDS(on)
Operated at Low Logic Level Gate Drive

V_{DS} -20 V
 I_D -0.75A
 $R_{DS(ON)}$ 420 m Ω

39K

Application

Load/Power Switching
Interfacing, Logic Switching
Battery Management for Ultra Small Portable Electronics



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-0.75	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-1.2	A
Power Dissipation ⁽²⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

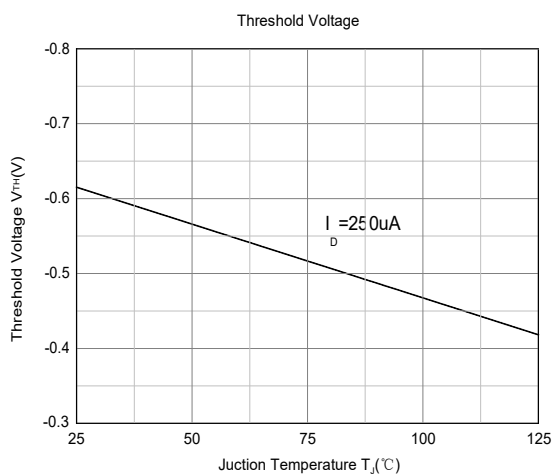
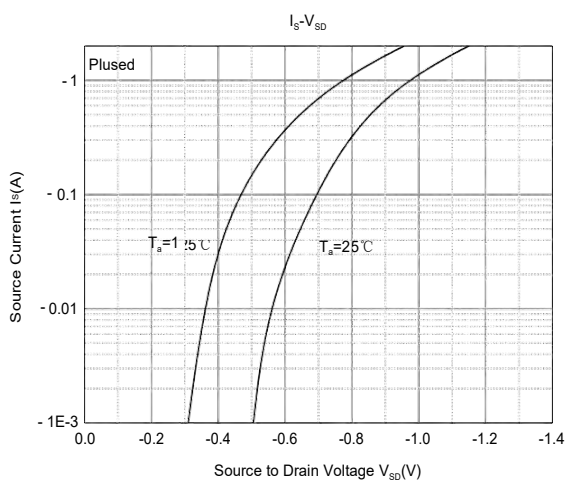
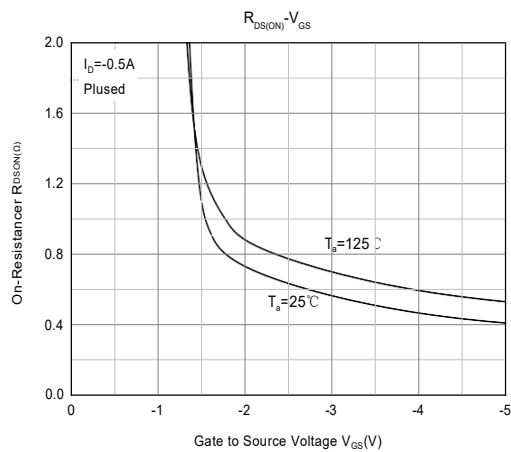
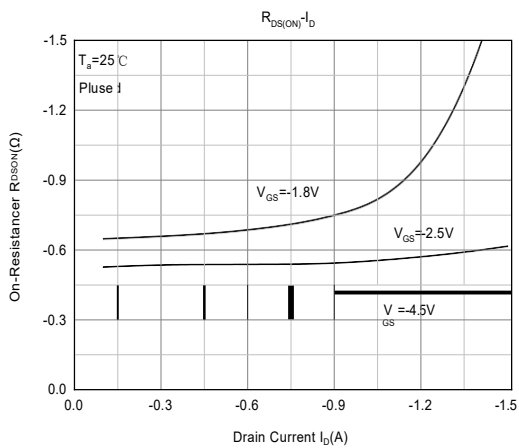
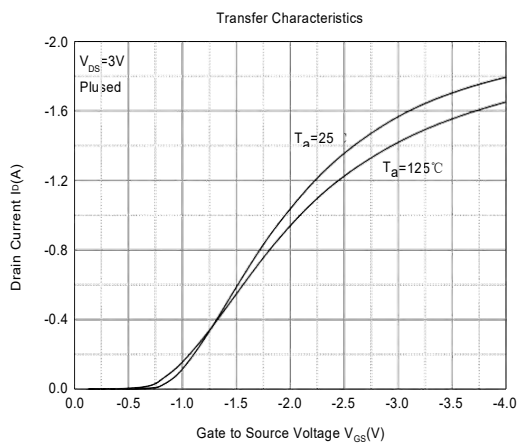
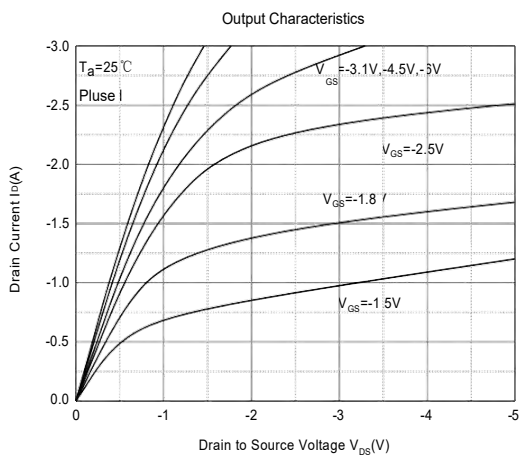
Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.61	-1.1	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1A		420	510	mΩ
		V _{GS} =-2.5V, I _D =-0.8A		630	750	
		V _{GS} =-1.8V, I _D =-0.5A		960		
Forward tranconductance	g _{FS}	V _{DS} =-10V, I _D =-0.54A	0.8			S
Dynamic characteristics ⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =-16V, V _{GS} =0V, f =1MHz		113		pF
Output Capacitance	C _{oss}			15		
Reverse Transfer Capacitance	C _{rss}			9		
Switching Characteristics ⁽⁴⁾						
Turn-on delay time	t _{d(on)}	V _{DS} =-10V, I _D =-200mA, V _{GS} =-4.5V, R _G =10Ω		9		ns
Turn-on rise time	t _r			5.7		
Turn-off delay time	t _{d(off)}			32.6		
Turn-off fall time	t _f			20.3		
Source-Drain Diode characteristics						
Diode forward voltage ⁽³⁾	V _{DS}	I _S =-0.5A, V _{GS} = 0V			-1.2	V

Notes:

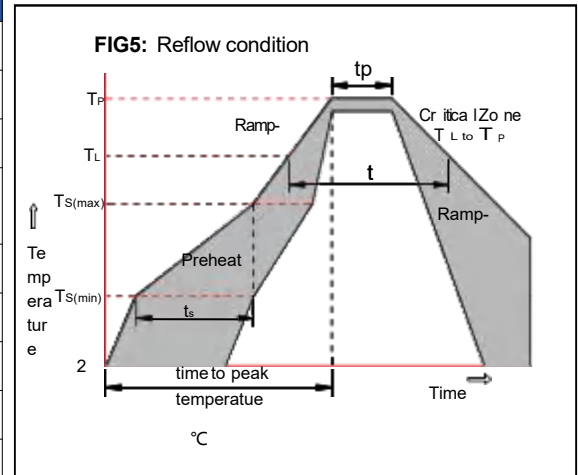
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_A=25^{\circ}\text{C}$.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.
4. These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES



Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

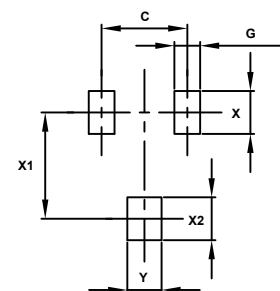


Package Dimensions & Suggested Pad Layout

SOT-523

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

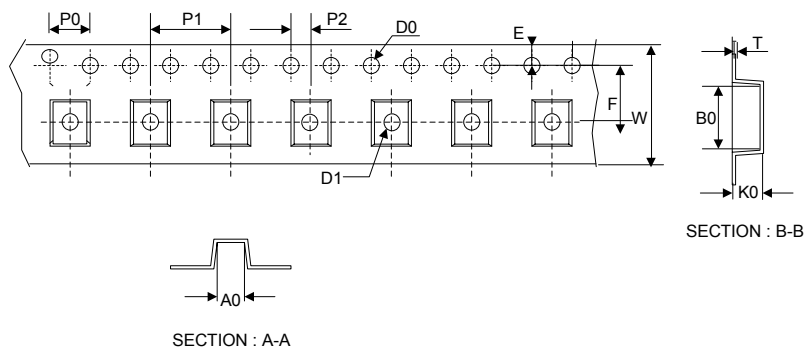
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	1.00
G	0.45
X	0.70
X1	1.40
X2	0.70
Y	0.60

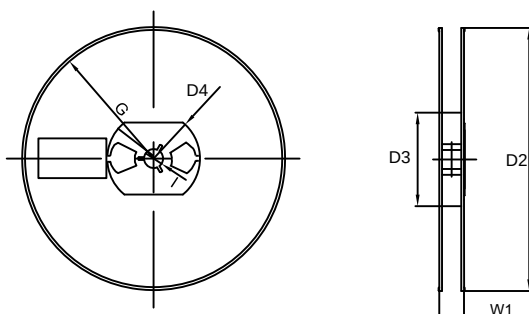
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	0.65±0.20
E	1.55±0.25
F	3.60±0.20
W	8.00±0.20
A0	2.10±0.20
B0	2.20±0.20
K0	1.10±0.20
T	0.20±0.20
D2	177.0±5.0
D3	55Min.
D4	R24.6±2.0
G	R82.0±2.0
I	13.0±2.0
W1	10.20±3.0

7" Reel



Quantity: 3000PCS